

Data Sheet

April 24, 2007

60MHz Rail-to-Rail Input-Output Op Amp

The EL5211A is a low power, high voltage, rail-to-rail inputoutput amplifier containing two amplifiers. Operating on supplies ranging from 5V to 15V, while consuming only 2.5mA per amplifier, the EL5211A has a bandwidth of 60MHz (-3dB) and provides common-mode input ability beyond the supply rails, as well as rail-to-rail output capability. This enables the EL5211A to offer maximum dynamic range at any supply voltage.

The EL5211A also features fast slewing and settling times, as well as a high output drive capability of 65mA (sink and source). These features make the EL5211A ideal for high speed filtering and signal conditioning application. Other applications include battery-powered, portable devices and anywhere low power consumption is important.

The EL5211A is available in the 8 Ld HMSOP package, features a standard operational amplifier pinout, and is specified for operation over a temperature range of -40°C to +85°C.

PART NUMBER (Note)	PART MARKING	TAPE & REEL	PACKAGE (Pb-free)	PKG. DWG. #
EL5211AIYEZ	BBLAA	-	8 Ld HMSOP (3.0mm)	MDP0050
EL5211AIYEZ-T7	BBLAA	7"	8 Ld HMSOP (3.0mm)	MDP0050
EL5211AIYEZ-T13	BBLAA	13"	8 Ld HMSOP (3.0mm)	MDP0050

Ordering Information

NOTE: Intersil Pb-free plus anneal products employ special Pb-free material sets; molding compounds/die attach materials and 100% matte tin plate termination finish, which are RoHS compliant and compatible with both SnPb and Pb-free soldering operations. Intersil Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020.

Features

- 60MHz (-3dB) bandwidth
- Supply voltage = 4.5V to 16.5V
- Low supply current (per amplifier) = 2.5mA
- High slew rate = 75V/µs
- Unity-gain stable
- Beyond the rails input capability
- · Rail-to-rail output swing
- ±110mA output short current
- · Pb-free plus anneal available (RoHS compliant)

Applications

- TFT-LCD panels
- V_{COM} amplifiers
- Drivers for A/D converters
- Data acquisition
- Video processing
- Audio processing
- Active filters
- Test equipment
- · Battery-powered applications
- · Portable equipment

Pinout





Absolute Maximum Ratings (T_A = +25°C)

Supply Voltage between V _S + and V _S	+18V
Input Voltage	V _S 0.5V, V _S +0.5V
Maximum Continuous Output Current	65mA
Maximum Die Temperature	+125°C

Thermal Information

Storage Temperature	-65°C to +150°C
Ambient Operating Temperature	40°C to +85°C
Power Dissipation	See Curves
Pb-free reflow profile	see link below
http://www.intersil.com/pbfree/Pb-FreeReflow.asp	C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

IMPORTANT NOTE: All parameters having Min/Max specifications are guaranteed. Typ values are for information purposes only. Unless otherwise noted, all tests are at the specified temperature and are pulsed tests, therefore: $T_J = T_C = T_A$

Electrical Specifications	$V_{S}\text{+}$ = +5V, $V_{S}\text{-}$ = -5V, R_{L} = 1k Ω to 0V, T_{A} = +25°C, Unless Otherw	ise Specified.
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PARAMETER	DESCRIPTION	CONDITIONS	MIN	TYP	MAX	UNIT			
INPUT CHARAC	INPUT CHARACTERISTICS								
V _{OS}	Input Offset Voltage	$V_{CM} = 0V$		3	15	mV			
TCV _{OS}	Average Offset Voltage Drift (Note 1)			7		µV/°C			
Ι _Β	Input Bias Current	$V_{CM} = 0V$		2	60	nA			
R _{IN}	Input Impedance			1		GΩ			
C _{IN}	Input Capacitance			2		pF			
CMIR	Common-Mode Input Range		-5.5		+5.5	V			
CMRR	Common-Mode Rejection Ratio	for V_{IN} from -5.5V to 5.5V	50	70		dB			
A _{VOL}	Open-Loop Gain	$-4.5V \le V_{OUT} \le 4.5V$	60	70		dB			
OUTPUT CHAR	ACTERISTICS								
V _{OL}	Output Swing Low	I _L = -5mA		-4.9	-4.8	V			
V _{OH}	Output Swing High	I _L = 5mA	4.8	4.9		V			
I _{SC}	Short-Circuit Current			±125		mA			
Ιουτ	Output Current			±65		mA			
POWER SUPPL	Y PERFORMANCE								
PSRR	Power Supply Rejection Ratio	$V_{\mbox{S}}$ is moved from ±2.25V to ±7.75V	60	80		dB			
I _S	Supply Current	No load		5	7.5	mA			
DYNAMIC PERF	FORMANCE								
SR	Slew Rate (Note 2)	-4.0V \leq V_{OUT} \leq 4.0V, 20% to 80%		75		V/µs			
t _S	Settling to +0.1% ($A_V = +1$)	$(A_V = +1), V_O = 2V \text{ step}$		80		ns			
BW	-3dB Bandwidth			60		MHz			
GBWP	Gain-Bandwidth Product			32		MHz			
PM	Phase Margin			50		o			
CS	Channel Separation	f = 5MHz		110		dB			
d _G	Differential Gain (Note 3)	$R_F = R_G = 1k\Omega$ and $V_{OUT} = 1.4V$		0.17		%			
dp	Differential Phase (Note 3)	$R_F = R_G = 1k\Omega$ and $V_{OUT} = 1.4V$		0.24		o			

NOTES:

1. Measured over operating temperature range.

2. Slew rate is measured on rising and falling edges.

3. NTSC signal generator used.

EL5211A

PARAMETER	DESCRIPTION	CONDITION	MIN	TYP	MAX	UNIT		
INPUT CHARACTERISTICS								
V _{OS}	Input Offset Voltage	$V_{CM} = 2.5V$		3	15	mV		
TCV _{OS}	Average Offset Voltage Drift (Note 4)			7		µV/°C		
IB	Input Bias Current	$V_{CM} = 2.5V$		2	60	nA		
R _{IN}	Input Impedance			1		GΩ		
C _{IN}	Input Capacitance			2		pF		
CMIR	Common-Mode Input Range		-0.5		+5.5	V		
CMRR	Common-Mode Rejection Ratio	for $V_{\mbox{\rm IN}}$ from -0.5V to 5.5V	45	66		dB		
A _{VOL}	Open-Loop Gain	$0.5V \leq V_{OUT} \leq 4.5V$	60	70		dB		
OUTPUT CHAR	ACTERISTICS							
V _{OL}	Output Swing Low	I _L = -5mA		100	200	mV		
V _{OH}	Output Swing High	I _L = 5mA	4.8	4.9		V		
I _{SC}	Short-Circuit Current			±125		mA		
IOUT	Output Current			±65		mA		
POWER SUPPL	Y PERFORMANCE							
PSRR	Power Supply Rejection Ratio	$V_{\mbox{\scriptsize S}}$ is moved from 4.5V to 15.5V	60	80		dB		
I _S	Supply Current	No load		5	7.5	mA		
DYNAMIC PERF	FORMANCE							
SR	Slew Rate (Note 5)	$1V \leq V_{OUT} \leq 4V,20\%$ to 80%		75		V/µs		
t _S	Settling to +0.1% ($A_V = +1$)	$(A_V = +1), V_O = 2V \text{ step}$		80		ns		
BW	-3dB Bandwidth			60		MHz		
GBWP	Gain-Bandwidth Product			32		MHz		
PM	Phase Margin			50		0		
CS	Channel Separation	f = 5MHz		110		dB		
d _G	Differential Gain (Note 6)	$R_F = R_G = 1 k\Omega$ and $V_{OUT} = 1.4 V$		0.17		%		
dP	Differential Phase (Note 6)	$R_F = R_G = 1k\Omega$ and $V_{OUT} = 1.4V$		0.24		o		

NOTES:

4. Measured over operating temperature range.

5. Slew rate is measured on rising and falling edges.

6. NTSC signal generator used.

$\label{eq:constraint} \textbf{Electrical Specifications} \quad \text{V}_{S^+} = +15\text{V}, \ \text{V}_{S^-} = 0\text{V}, \ \text{R}_L = 1\text{k}\Omega \ \text{to} \ 7.5\text{V}, \ \text{T}_A = +25^\circ\text{C}, \ \text{Unless Otherwise Specified}.$

PARAMETER	DESCRIPTION	CONDITION	MIN	TYP	MAX	UNIT		
INPUT CHARAC	NPUT CHARACTERISTICS							
V _{OS}	Input Offset Voltage	V _{CM} = 7.5V		3	15	mV		
TCV _{OS}	Average Offset Voltage Drift (Note 7)			7		µV/°C		
I _B	Input Bias Current	V _{CM} = 7.5V		2	60	nA		
R _{IN}	Input Impedance			1		GΩ		
C _{IN}	Input Capacitance			2		pF		
CMIR	Common-Mode Input Range		-0.5		+15.5	V		

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PARAMETER	DESCRIPTION	CONDITION	MIN	TYP	MAX	UNIT
CMRR	Common-Mode Rejection Ratio	for V _{IN} from -0.5V to 15.5V	53	72		dB
A _{VOL}	Open-Loop Gain	$0.5V \le V_{OUT} \le 14.5V$	60	70		dB
OUTPUT CHAR	ACTERISTICS		I			
V _{OL}	Output Swing Low	I _L = -5mA		100	200	mV
V _{OH}	Output Swing High	I _L = 5mA	14.8	14.9		V
I _{SC}	Short-Circuit Current			±125		mA
IOUT	Output Current			±65		mA
POWER SUPPL	YPERFORMANCE					
PSRR	Power Supply Rejection Ratio	$\rm V_S$ is moved from 4.5V to 15.5V	60	80		dB
IS	Supply Current	No load		5	7.5	mA
DYNAMIC PERI	FORMANCE					
SR	Slew Rate (Note 8)	$1V \leq V_{OUT} \leq 14V,20\%$ to 80%		75		V/µs
t _S	Settling to +0.1% ($A_V = +1$)	$(A_V = +1), V_O = 2V \text{ step}$		80		ns
BW	-3dB Bandwidth			60		MHz
GBWP	Gain-Bandwidth Product			32		MHz
PM	Phase Margin			50		0
CS	Channel Separation	f = 5MHz		110		dB
d _G	Differential Gain (Note 9)	R_{F} = R_{G} = 1k Ω and V_{OUT} = 1.4V		0.16		%
dP	Differential Phase (Note 9)	$R_F = R_G = 1k\Omega$ and $V_{OUT} = 1.4V$		0.22		0

NOTES:

7. Measured over operating temperature range.

8. Slew rate is measured on rising and falling edges.

9. NTSC signal generator used.

Typical Performance Curves





..... -1 0 :::: - 4 :



FIGURE 3. INPUT OFFSET VOLTAGE vs TEMPERATURE



FIGURE 4. INPUT BIAS CURRENT vs TEMPERATURE



FIGURE 5. OUTPUT HIGH VOLTAGE vs TEMPERATURE



FIGURE 7. OPEN-LOOP GAIN vs TEMPERATURE



FIGURE 6. OUTPUT LOW VOLTAGE vs TEMPERATURE



FIGURE 8. SLEW RATE vs TEMPERATURE



FIGURE 9. SUPPLY CURRENT PER AMPLIFIER vs SUPPLY VOLTAGE



FIGURE 10. SUPPLY CURRENT PER AMPLIFIER vs TEMPERATURE



FIGURE 11. DIFFERENTIAL GAIN



FIGURE 13. HARMONIC DISTORTION vs VOP-P

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FIGURE 12. DIFFERENTIAL PHASE



FIGURE 14. OPEN LOOP GAIN AND PHASE

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FIGURE 15. FREQUENCY RESPONSE FOR VARIOUS RL



FIGURE 17. CLOSED LOOP OUTPUT IMPEDANCE





FIGURE 16. FREQUENCY RESPONSE FOR VARIOUS CL







FIGURE 20. PSRR



FIGURE 21. INPUT VOLTAGE NOISE SPECTRAL DENSITY



FIGURE 22. CHANNEL SEPARATION



FIGURE 23. SMALL-SIGNAL OVERSHOOT vs LOAD CAPACITANCE



FIGURE 24. SETTLING TIME vs STEP SIZE



FIGURE 26. SMALL SIGNAL TRANSIENT RESPONSE

 $\frac{IBCrow}{T_A} = +25^{\circ}C - A_V = 1$ $R_L = 1k\Omega$ 1V STEP 50ns/DIV



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Pin Descriptions

PIN NUMBER	PIN NAME	FUNCTION	EQUIVALENT CIRCUIT
1	VOUTA	Amplifier A output	VS+ VS+ VS+ VS+ VS- GND VS- CIRCUIT 1
2	VINA-	Amplifier A inverting input	VS+ VS+ VS+ VS+ VS- VS- VS- VS- VS- VS- VS- VS-
3	VINA+	Amplifier A non-inverting input	(Reference Circuit 2)
4	VS-	Negative power supply	
5	VINB+	Amplifier B non-inverting input	(Reference Circuit 2)
6	VINB-	Amplifier B inverting input	(Reference Circuit 2)
7	VOUTB	Amplifier B output	(Reference Circuit 1)
8	VS+	Positive power supply	

Applications Information

Product Description

The EL5211A voltage feedback amplifier is fabricated using a high voltage CMOS process. It exhibits rail-to-rail input and output capability, is unity gain stable, and has low power consumption (2.5mA per amplifier). These features make the EL5211A ideal for a wide range of general-purpose applications. Connected in voltage follower mode and driving a load of 1k Ω , the EL5211A has a -3dB bandwidth of 60MHz while maintaining a 75V/µs slew rate. The EL5211A is a dual amplifier.

Operating Voltage, Input, and Output

The EL5211A is specified with a single nominal supply voltage from 5V to 15V or a split supply with its total range from 5V to 15V. Correct operation is guaranteed for a supply range of 4.5V to 16.5V. Most EL5211A specifications are stable over both the full supply range and operating temperatures of -40°C to +85°C. Parameter variations with operating voltage and/or temperature are shown in the "Typical Performance Curves" on page 4.

The input common-mode voltage range of the EL5211A extends 500mV beyond the supply rails. The output swings of the EL5211A typically extend to within 100mV of positive and negative supply rails with load currents of 5mA. Decreasing load currents will extend the output voltage

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range even closer to the supply rails. Figure 27 shows the input and output waveforms for the device in the unity-gain configuration. Operation is from $\pm 5V$ supply with a 1k Ω load connected to GND. The input is a 10V_{P-P} sinusoid. The output voltage is approximately 9.8V_{P-P}.



FIGURE 27. OPERATION WITH RAIL-TO-RAIL INPUT AND OUTPUT

Short Circuit Current Limit

The EL5211A will limit the short circuit current to \pm 110mA if the output is directly shorted to the positive or the negative supply. If an output is shorted indefinitely, the power dissipation could easily increase such that the device may be damaged. Maximum reliability is maintained if the output continuous current never exceeds \pm 65mA. This limit is set by the design of the internal metal interconnects.

Output Phase Reversal

The EL5211A is immune to phase reversal as long as the input voltage is limited from V_S- 0.5V to V_S+ 0.5V. Figure 28 shows a photo of the output of the device with the input voltage driven beyond the supply rails. Although the device's output will not change phase, the input's overvoltage should be avoided. If an input voltage exceeds supply voltage by more than 0.6V, electrostatic protection diodes placed in the input stage of the device begin to conduct and overvoltage damage could occur.



FIGURE 28. OPERATION WITH BEYOND-THE-RAILS INPUT

Power Dissipation

With the high-output drive capability of the EL5211A amplifier, it is possible to exceed the +125°C absolute maximum junction temperature under certain load current conditions. Therefore, it is important to calculate the maximum junction temperature for the application to determine if load conditions need to be modified for the amplifier to remain in the safe operating area.

The maximum power dissipation allowed in a package is determined according to:

$$P_{DMAX} = \frac{T_{JMAX} - T_{AMAX}}{\Theta_{JA}}$$
(EQ. 1)

where:

- T_{JMAX} = Maximum junction temperature
- T_{AMAX} = Maximum ambient temperature
- Θ_{JA} = Thermal resistance of the package
- P_{DMAX} = Maximum power dissipation in the package

The maximum power dissipation actually produced by an IC is the total quiescent supply current times the total power supply voltage, plus the power in the IC due to the loads, or:

$$P_{DMAX} = \Sigma i [V_S \times I_{SMAX} + (V_S + -V_{OUT}i) \times I_{LOAD}i]$$
(EQ. 2)

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when sourcing, and:

$$P_{DMAX} = \Sigma i [V_S \times I_{SMAX} + (V_{OUT}i - V_S^-) \times I_{LOAD}i]$$
(EQ. 3)

when sinking,

where:

- i = 1 to 2 for dual and 1 to 4 for quad
- V_S = Total supply voltage
- I_{SMAX} = Maximum supply current per amplifier
- V_{OUT}i = Maximum output voltage of the application
- ILOADi = Load current

If we set the two P_{DMAX} equations equal to each other, we can solve for R_{LOAD} to avoid device overheat. Figures 29 and 30 provide a convenient way to see if the device will overheat. The maximum safe power dissipation can be found graphically, based on the package type and the ambient temperature. By using the Equation 3, it is a simple matter to see if P_{DMAX} exceeds the device's power derating curves. To ensure proper operation, it is important to observe the recommended derating curves shown in Figures 29 and 30.



FIGURE 29. PACKAGE POWER DISSIPATION vs AMBIENT TEMPERATURE



FIGURE 30. PACKAGE POWER DISSIPATION vs AMBIENT TEMPERATURE

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Unused Amplifiers

It is recommended that any unused amplifiers in a dual and a quad package be configured as a unity gain follower. The inverting input should be directly connected to the output and the non-inverting input tied to the ground plane.

Power Supply Bypassing and Printed Circuit Board Layout

The EL5211A can provide gain at high frequency. As with any high-frequency device, good printed circuit board layout is necessary for optimum performance. Ground plane construction is highly recommended, lead lengths should be as short as possible and the power supply pins must be well bypassed to reduce the risk of oscillation. For normal single supply operation, where the V_S- pin is connected to ground, a 0.1µF ceramic capacitor should be placed from V_S+ to pin to V_S- pin. A 4.7µF tantalum capacitor should then be connected in parallel, placed in the region of the amplifier. One 4.7µF capacitor may be used for multiple devices. This same capacitor combination should be placed at each supply pin to ground if split supplies are to be used.

HMSOP (Heat-Sink MSOP) Package Family







BOTTOM VIEW







MDP0050

HMSOP (HEAT-SINK MSOP) PACKAGE FAMILY

	MILLIMETERS					
SYMBOL	HMSOP8	HMSOP10	TOLERANCE	NOTES		
А	1.00	1.00	Max.	-		
A1	0.075	0.075	+0.025/-0.050	-		
A2	0.86	0.86	±0.09	-		
b	0.30	0.20	+0.07/-0.08	-		
С	0.15	0.15	±0.05	-		
D	3.00	3.00	±0.10	1, 3		
D1	1.85	1.85	Reference	-		
Е	4.90	4.90	±0.15	-		
E1	3.00	3.00	±0.10	2, 3		
E2	1.73	1.73	Reference	-		
е	0.65	0.50	Basic	-		
L	0.55	0.55	±0.15	-		
L1	0.95	0.95	Basic	-		
Ν	8	10	Reference	-		
Rev. 1.2/07						

NOTES:

- 1. Plastic or metal protrusions of 0.15mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25mm maximum per side are not included.
- 3. Dimensions "D" and "E1" are measured at Datum Plane "H".
- 4. Dimensioning and tolerancing per ASME Y14.5M-1994.

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